

DDR3 SI/PI Analysis using IBIS5.0

Shintaro Ohtani FUJITSU SEMICONDUCTOR LIMITED

Asian IBIS Summit Yokohama, Japan November 18, 2011

Copyright 2011 FUJITSU SEMICONDUCTOR LIMITED





- Problems of DDR3 SI/PI Analysis
- DDR3 SI/PI Analysis using IBIS5.0
- Summary
- Expecting of IBIS



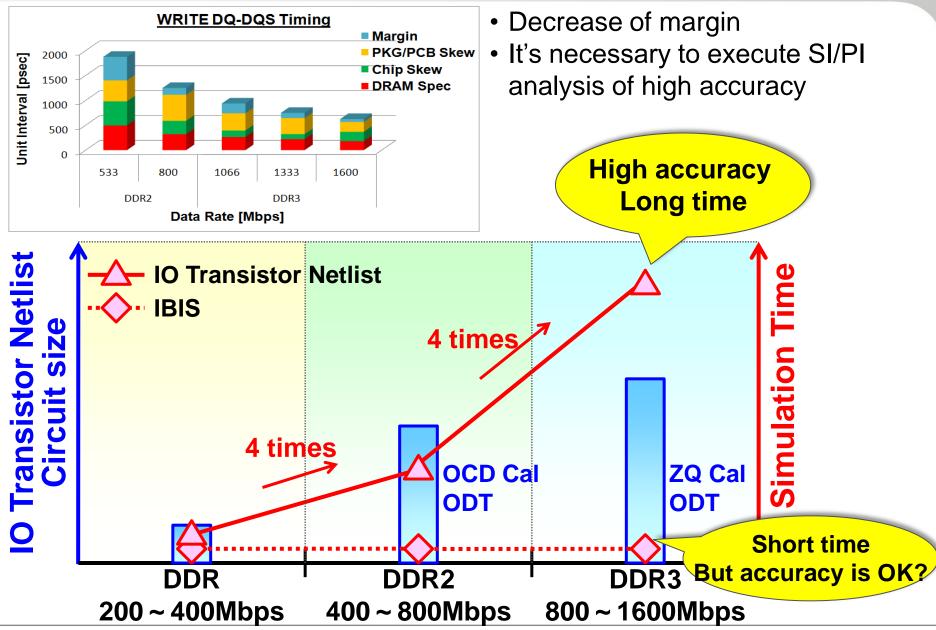


DDR3 SI/PI Analysis using IBIS5.0

Summary

Expecting of IBIS







Contents

IO Transistor Netlist	IBIS	
Detailed circuits and netlists (transistor level)	I-V/V-T tables for IO final buffer	

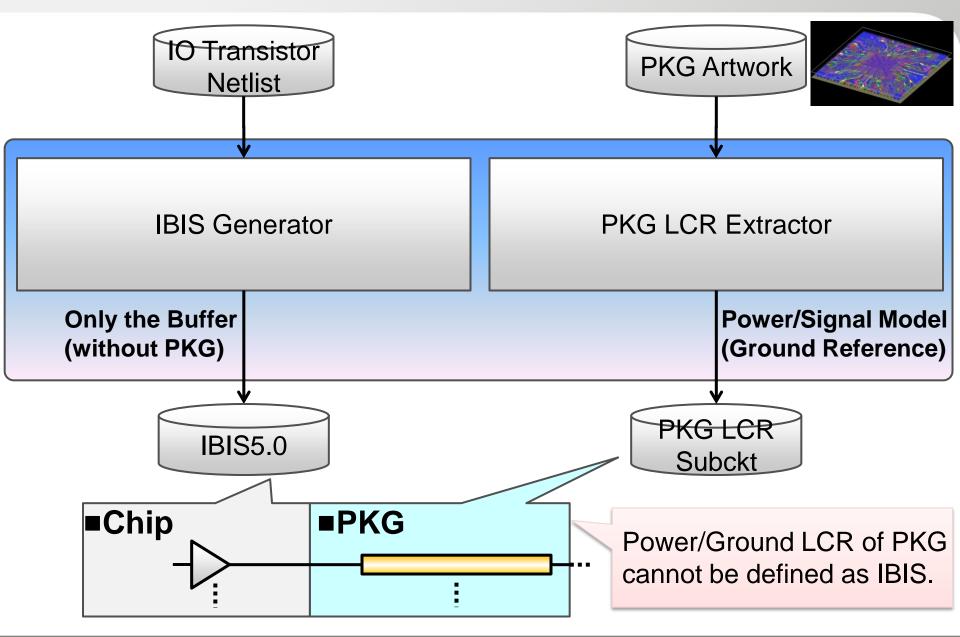
Trade-off

	IO Transistor Netlist	IBIS	
Simulation Time	Slow (Several to 10 times slower than IBIS)	Fast	
Format	Bad (Encryption and NDA are necessary)	Good (Open format)	
EDA Tools Utilization	Bad (Specific simulator is necessary for encrypted models)	Good (Many SI/PI tools support)	
Accuracy (SI)	Good	Reasonably good	
Accuracy (PI)	Good	? (Supported SSO from Ver.5.0)	

We have evaluated an ability of IBIS5.0 in terms of SI/PI.

IBIS5.0 Generation









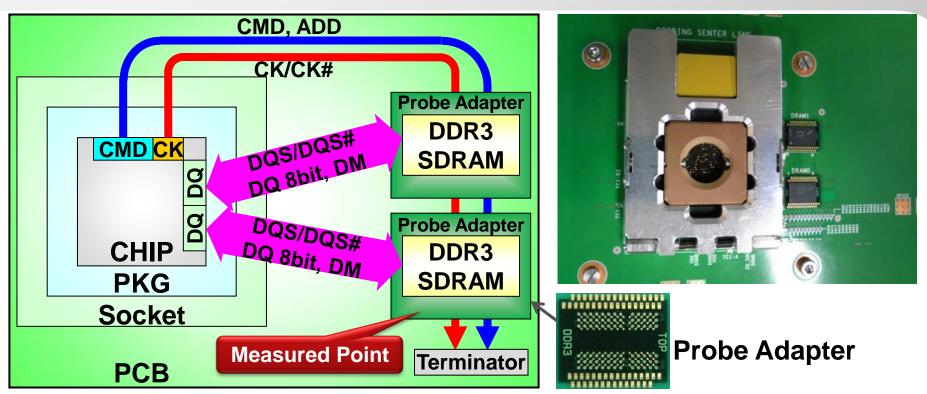
DDR3 SI/PI Analysis using IBIS5.0

Summary

Expecting of IBIS

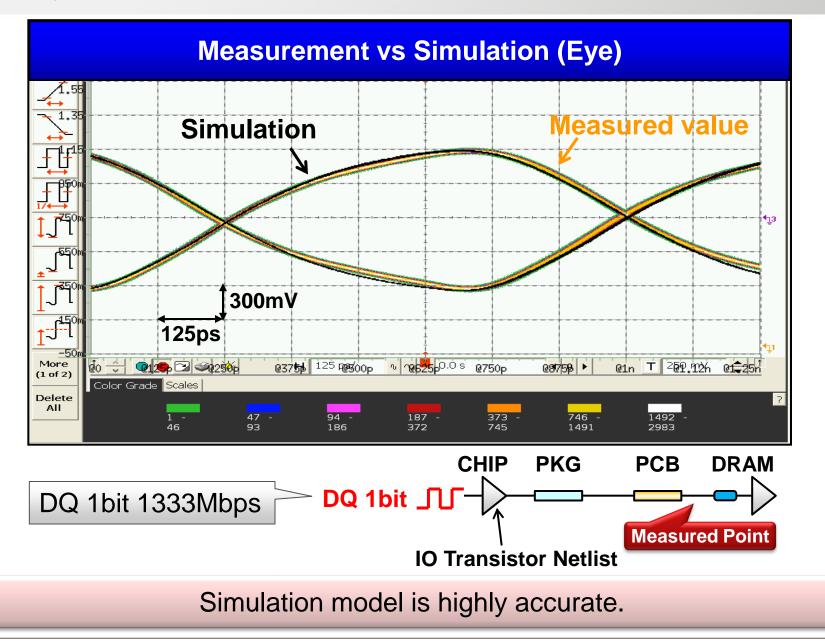
Evaluation Environment





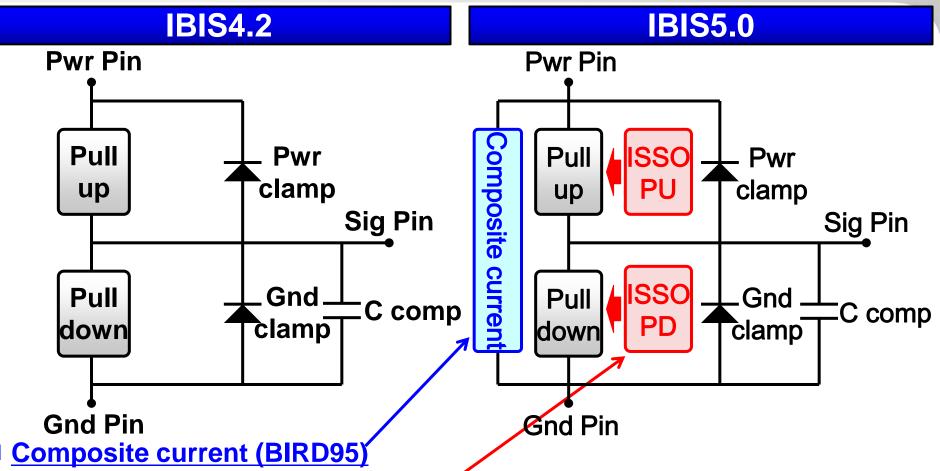
Item	Explanation	
CHIP	65nm DDR3 Interface Test Chip 16bit	
(mounted on Socket)	Data Rate : 1333Mbps	
PKG	Wire Bond BGA 4Layer 900ball 31mmx31mm	
PCB	6Layer	
DRAM	DDR3 SDRAM 8bitx2 on Board	
(mounted on Probe Adapter) (Fly-by architecture)		

Validity of Simulation Model



IBIS4.2 vs IBIS5.0



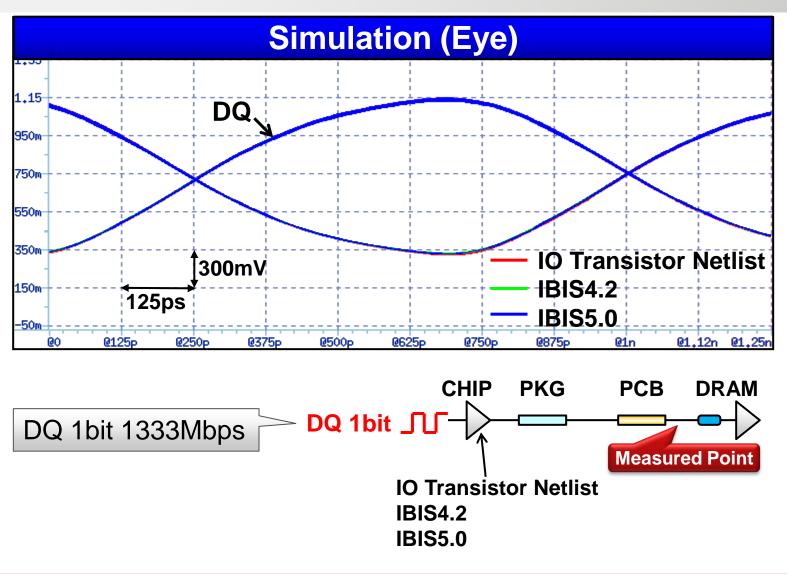


Characterizes currents from the supply rail through the buffer, as the buffer switches into a known load. It can show accurately driving current of IO.

ISSO PU / ISSO PD (BIRD98)

Characterizes buffer current modulation due to supply variation. It can show a change of driving current by voltage fluctuation.

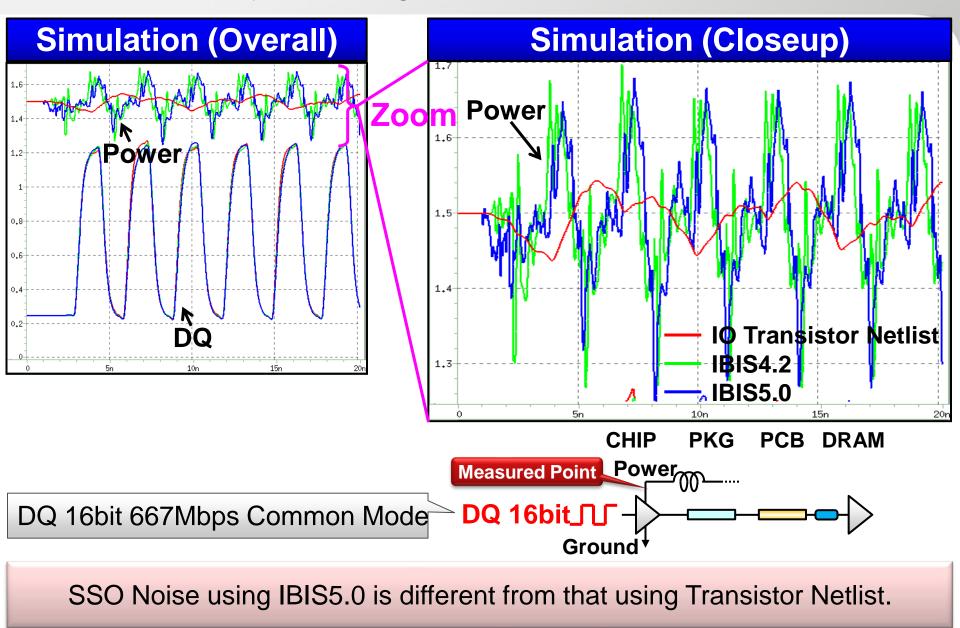
DDR3 SI Analysis using IBIS5.0



Both IBIS4.2 and IBIS5.0 are highly accurate.(in case SI analysis)

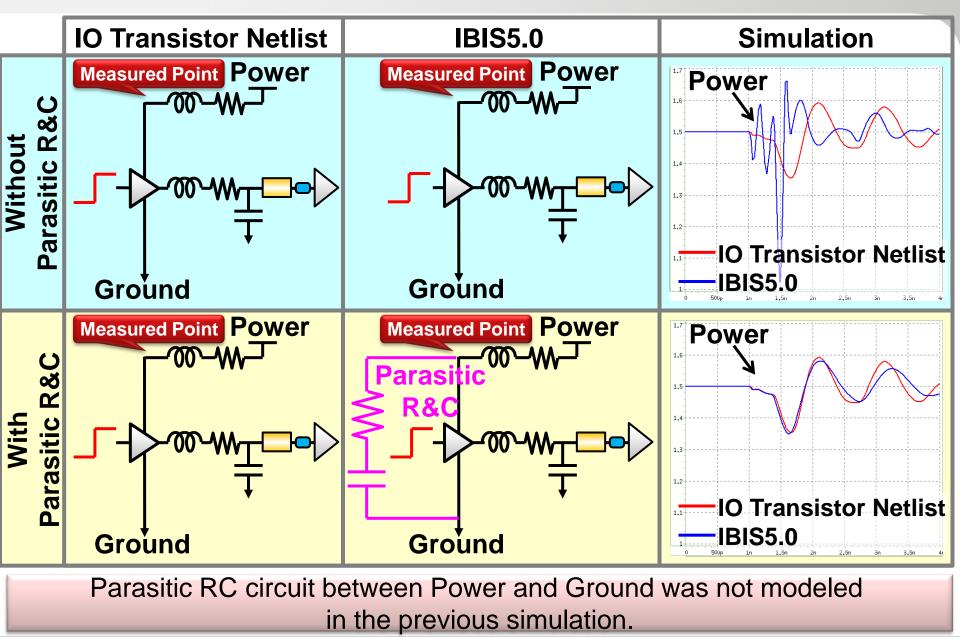
DDR3 PI Analysis using IBIS5.0 (SSO Noise)





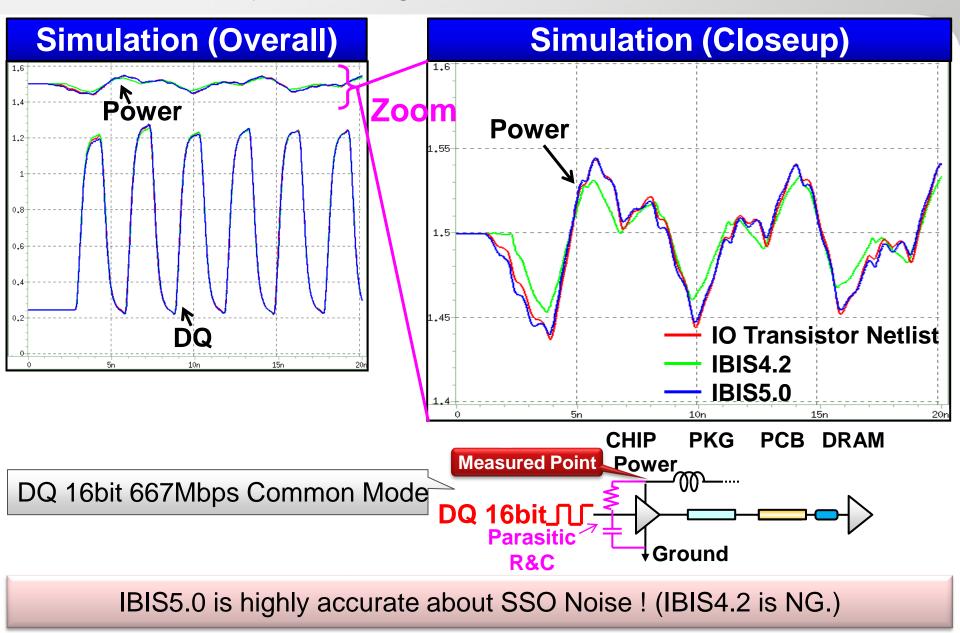
Reason that SSO Noise is different





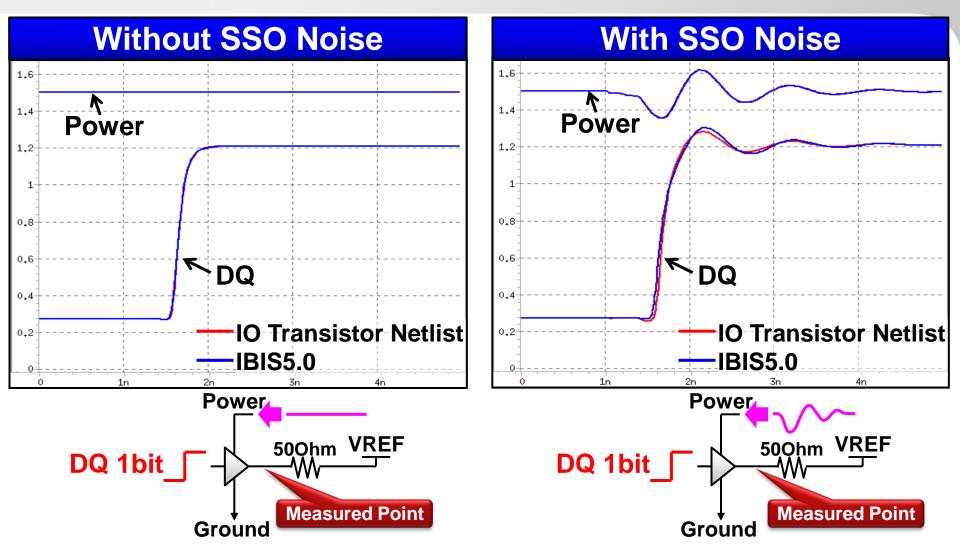
DDR3 PI Analysis using IBIS5.0 (Improved)





DDR3 PI Analysis using IBIS5.0 (Signal)

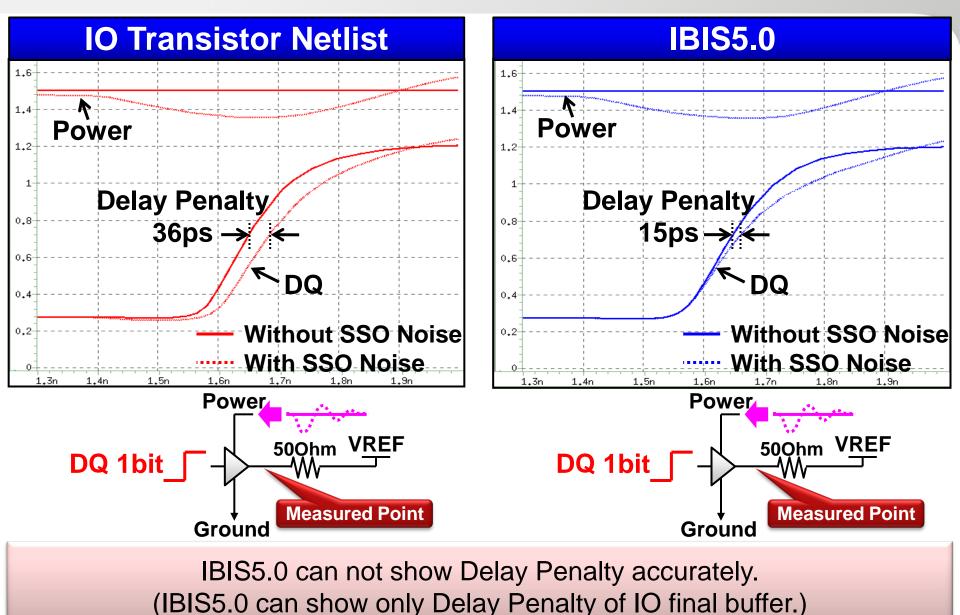




IBIS5.0 can show signal distortion related to SSO Noise.

DDR3 PI Analysis using IBIS5.0 (Delay Penalty)









DDR3 SI/PI Analysis using IBIS5.0

Summary

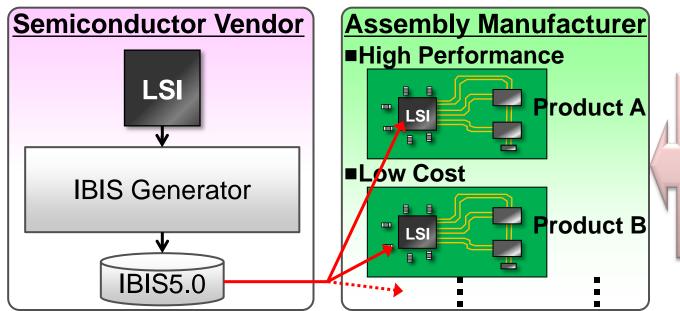
Expecting of IBIS

Summary



ltem	IO Transistor Netlist	IBIS5.0	IBIS4.2		
SI (Ideal Power)	0	0	0		
PI (SSO Noise)	0	0	×		
PI (Signal)	0	0	×		
PI (Delay Penalty)	0	Δ	×		
Sim. time %1	1020 minutes	24 minutes	24 minutes		
%1. 50ns Transient Analysis97% Down					

If we can show Delay Penalty accurately in IBIS5.0 ...



We can execute SI/Timing analysis that includes PI influence accurately and shortly !





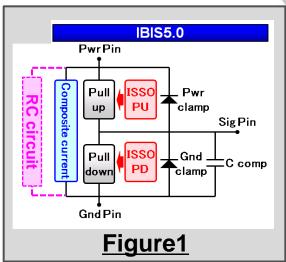
- Problems of DDR3 SI/PI Analysis
- DDR3 SI/PI Analysis using IBIS5.0
- Summary
 - Expecting of IBIS

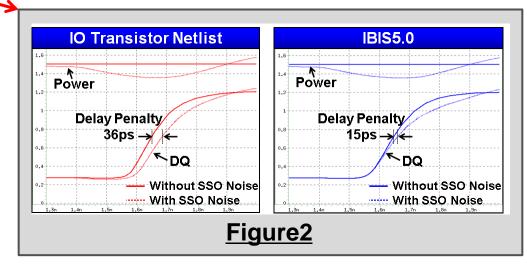
Expecting of IBIS



Problems in IBIS5.0

- It's impossible to define Power/Ground LCR of PKG in IBIS5.0
- Parasitic RC circuit doesn't exist in a circuit defined as IBIS5.0(Refer to Figure1) ——
- IBIS5.0 can not show IO Delay Penalty accurately (Refer to Figure2)





Please improve above-mentioned problems in IBIS5.0.

FUJTSU

shaping tomorrow with you